

isc N-Channel MOSFET Transistor

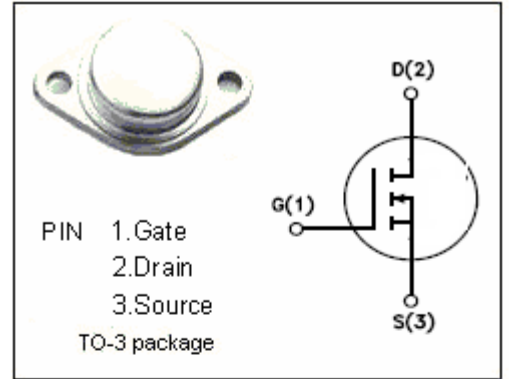
2N6761

DESCRIPTION

- VGS Rated at ±20V
- Silicon Gate for fast switching speeds
- IDSS、RDS(ON), specified at elevated temperature
- Low drive requirements

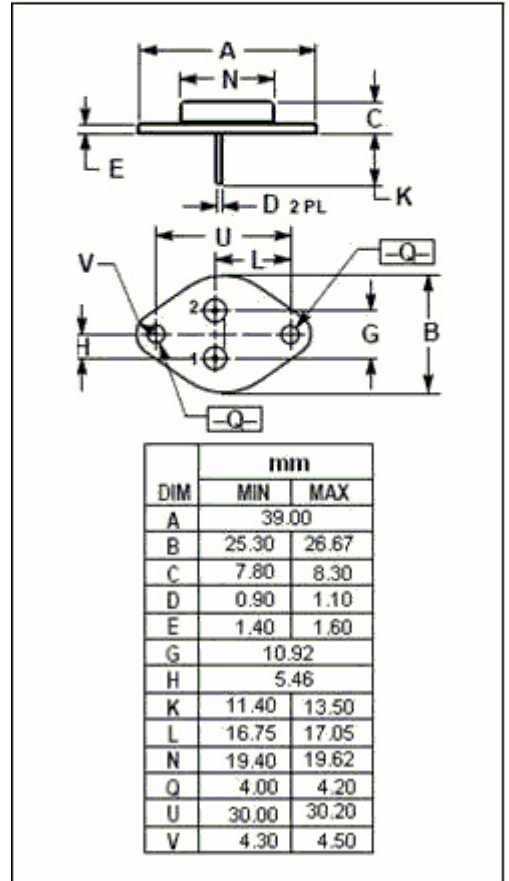
APPLICATIONS

designed for high power, high speed application, such as switching applies, UPS, AC and DC motor controls, relay and high energy pulse circuits.



ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage (V _{GS} =0)	450	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current-continuous@ TC=37°C	4.0	A
P _{tot}	Total Dissipation@TC=25°C	75	W
T _j	Max. Operating Junction Temperature	-55~150	°C
T _{stg}	Storage Temperature Range	-55~150	°C



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	1.67	°C/W

isc N-Channel Mosfet Transistor**2N6761****• ELECTRICAL CHARACTERISTICS (T_C=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = 1mA	450		V
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D = 1mA	2	4	V
R _{DS(ON)}	Drain-Source On-stage Resistance	V _{GS} = 10V; I _D = 2.5A		2.0	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = 20V; V _{DS} = 0		100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 450V; V _{GS} = 0		1	mA
V _{SD}	Diode Forward Voltage	I _F = 4.0A; V _{GS} = 0		1.3	V